

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	91	(III near2 nitride or gan or algan or ingan or gallium near nitride) same (uniform\$4 or variance or varying or consisten\$4) near3 (doping or (dopant or carrier or hole or electron or impurity) near (concentration or density))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 11:04
S2	3	("6447604"   "6468882"   "6642546").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/05 13:31
S3	963	(III near2 nitride or gan or algan or ingan or gallium near nitride) near8 (ti or titanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/05 15:41
S4	21	(III near2 nitride or gan or algan or ingan or gallium near nitride) same (fielo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 12:20
S5	58	(III near2 nitride or gan or algan or ingan or gallium near nitride) near10 (mocvd or hvpe or omvpe or cvd or growth or deposition) near8 (ti or titanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 11:05
S6	3	("20020197825"   "20030183157"   "6579359").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/06 10:48
S7	8	(III near2 nitride or gan or algan or ingan or gallium near nitride) same (void or pit or pore or porous or pitted or pitting) near8 (filled or filling or smooth or smoothing or remove or removal or removing or fill) near8 (heat or heating or heated or anneal\$4 or thermal\$2 or cure or curing or cured or hydrogen or h)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 11:13
S8	76	(III near2 nitride or gan or algan or ingan or gallium near nitride) same (void or pit or pore or porous or pitted or pitting) near8 (heat or heating or heated or anneal\$4 or thermal\$2 or cure or curing or cured or hydrogen or h)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 14:27

## EAST Search History

S9	13	("5185290"   "5798536"   "6051849"   "6110277"   "6121121"   "6146457"   "6153010"   "6274518"   "6319742"   "6329667"   "6355497"   "6365921"   "6380108").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/06 13:05
S10	1059	(III near2 nitride or gan or algan or ingan or gallium near nitride) near6 (doped or doping or dopant or impurity or silane or silicon or si) and (hvpe or halide near vpe or halide near vapor near phase near epitaxy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 14:28
S11	187	(III near2 nitride or gan or algan or ingan or gallium near nitride) near6 (doped or doping or dopant or impurity) same (hvpe or halide near vpe or halide near vapor near phase near epitaxy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 14:28
S12	102	(III near2 nitride or gan or algan or ingan or gallium near nitride) near6 (doped or doping or dopant or impurity) same (hvpe or halide near vpe or halide near vapor near phase near epitaxy) and (doping or dopant or impurity or doped or silicon or magnesium or p or n) near6 (uniform\$4 or consisten\$4 or constant or within or chang\$4 or unvary\$4 or nonvary\$4 or identical or similar)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 14:35
S13	116	(III near2 nitride or gan or algan or ingan or gallium near nitride) near6 (doped or doping or dopant or impurity) same (hvpe or halide near vpe or halide near vapor near phase near epitaxy) and (doping or dopant or impurity or doped or silicon or magnesium or p or n or carrier or hole or electron) near6 (uniform\$4 or consisten\$4 or constant or within or chang\$4 or unvary\$4 or nonvary\$4 or identical or similar)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 16:40
S14	13	(US-20060097353-\$ or US-20050142682-\$ or US-20030134493-\$ or US-20020081763-\$ or US-20020197825-\$ or US-20030017685-\$ or US-20030070607-\$).did. or (US-6773504-\$ or US-6921678-\$ or US-6596079-\$ or US-6447604-\$).did. or (EP-1246233-\$).did. or (JP-2002343728-\$).did.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/09/06 16:29

## EAST Search History

S15	2	(III near2 nitride or gan or algan or ingan or gallium near nitride) near6 (doped or doping or dopant or impurity) same (hvpe or halide near vpe or halide near vapor near phase near epitaxy) and (increas\$4 or greater or more or additional or heightened) near6 (pressure or atm or torr) near6 (gacl or gallium near chloride or ga near cl)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 16:45
S16	65	(III near2 nitride or gan or algan or ingan or gallium near nitride) near6 (doped or doping or dopant or impurity) same (hvpe or halide near vpe or halide near vapor near phase near epitaxy) and (gas or carrier or ambient) near4 (h or hydrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 16:46
S17	338	257/76.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 11:19
S18	371	257/615.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 11:30
S19	190	257/631.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 11:38
S20	1638	117/89.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 11:52
S21	132	117/89.ccls. and (gan or algan or ingan or inalgan or gallium near nitride or ga near n or iii near nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 12:03
S22	262	117/93.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 12:03

## EAST Search History

S23	904	117/102.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 12:07
S24	51	117/102.ccls. and (gan or algan or ingan or inalgan or gallium near nitride or ga near n or iii near nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 12:04
S25	761	117/105.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 12:07
S26	69	(III near2 nitride or gan or algan or ingan or gallium near nitride or ga! near n) near8 (void or voided or pitted or pit or pore or porous or notch) and (epitaxial or hvpe or mocvd or movpe or omvpe or elo or growth or overgrowth) near8 (ti or titanium or sio or silicon near oxide or silicon near dioxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/07 12:23